

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

2SJ200

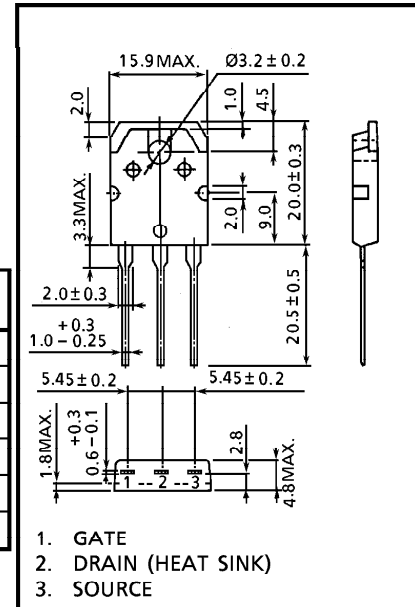
HIGH POWER AMPLIFIER APPLICATION

Unit in mm

- High Breakdown Voltage : $V_{DSS} = -180V$
- High Forward Transfer Admittance : $|Y_{fs}| = 4.0S$ (Typ.)
- Complementary to 2SK1529

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	-180	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	-10	A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	120	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

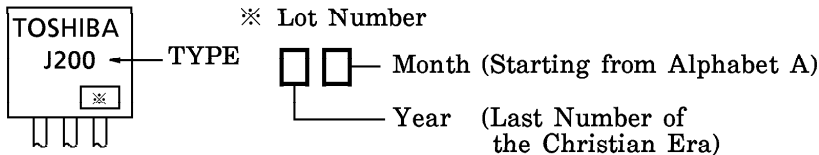


1. GATE
2. DRAIN (HEAT SINK)
3. SOURCE

JEDEC	—
EIAJ	SC-65
TOSHIBA	2-16C1B

Weight : 4.7g

MARKING



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	I_{DSS}	$V_{DS} = -180V, V_{GS} = 0$	—	—	-1.0	mA
Gate Leakage Current	I_{GSS}	$V_{DS} = 0, V_{GS} = \pm 20V$	—	—	± 0.5	μA
Drain-Source Breakdown Voltage	$V(BR)_{DSS}$	$I_D = -10mA, V_{GS} = 0$	-180	—	—	V
Gate-Source Cut-Off Voltage	$V_{GS(OFF)}$ (Note)	$V_{DS} = -10V, I_D = -0.1A$	-0.8	—	-2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D = -6A, V_{GS} = -10V$	—	-1.5	-5.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -3A$	—	4.0	—	S
Input Capacitance	C_{iss}	$V_{DS} = -30V, V_{GS} = 0, f = 1MHz$	—	1300	—	pF
Output Capacitance	C_{oss}	$V_{DS} = -30V, V_{GS} = 0, f = 1MHz$	—	350	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -30V, V_{GS} = 0, f = 1MHz$	—	200	—	pF

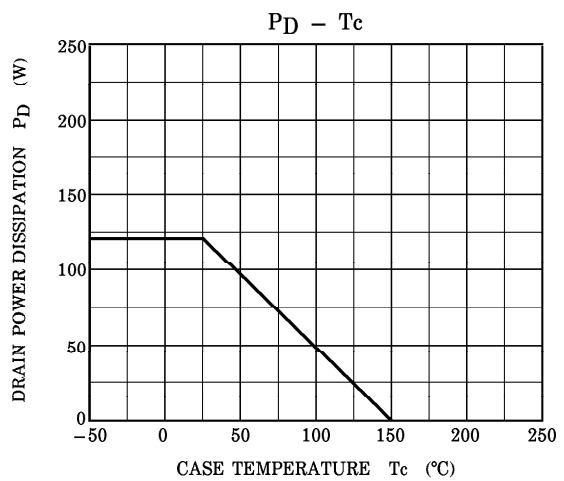
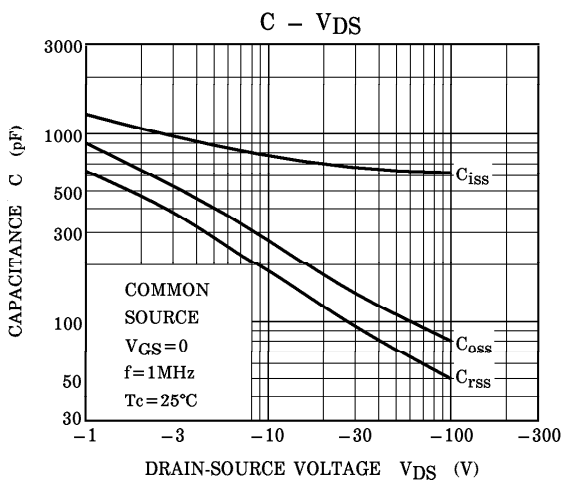
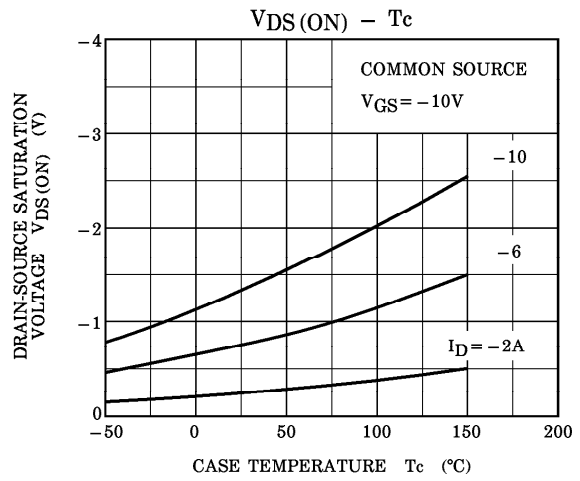
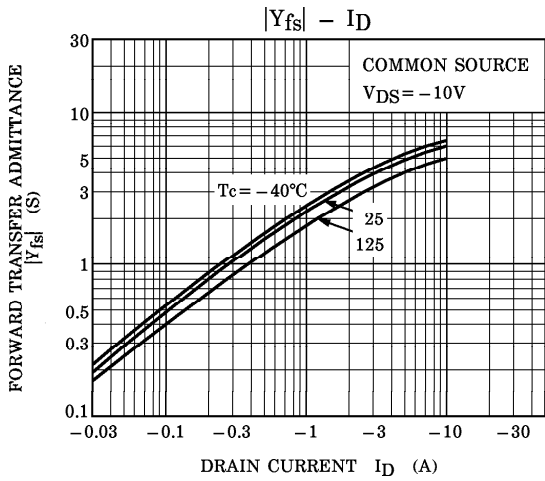
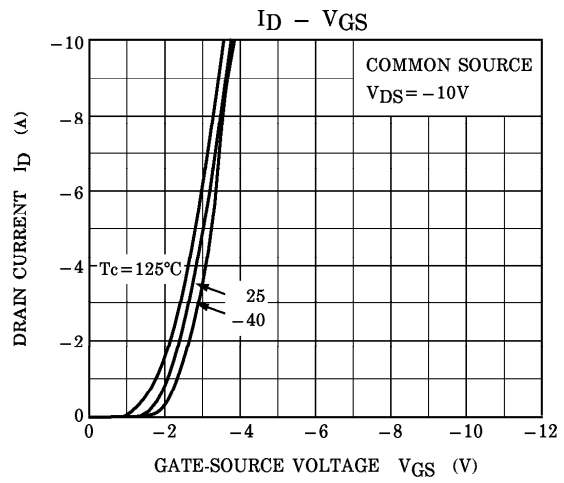
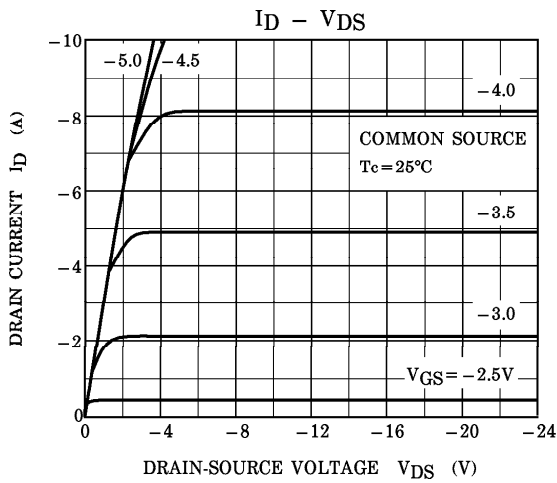
(Note) $V_{GS(OFF)}$ Classification O : -0.8~-1.6, Y : -1.4~-2.8

This transistor is an electrostatic sensitive device.

Please handle with caution.

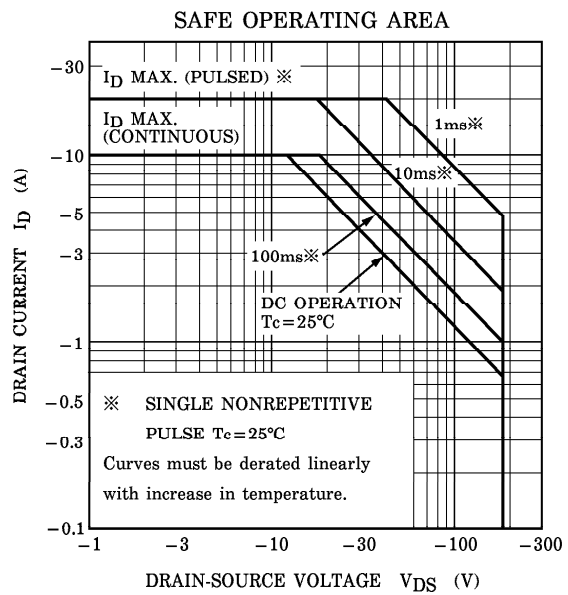
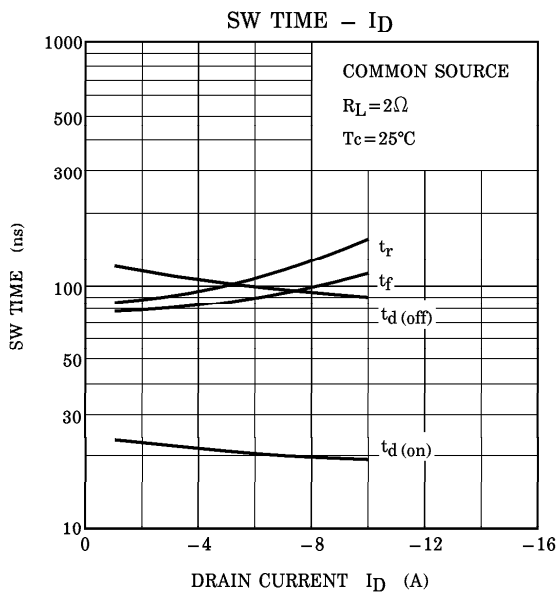
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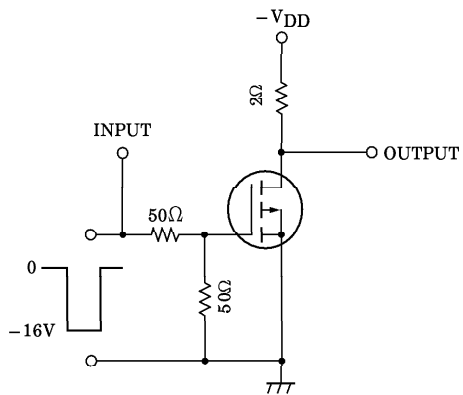


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SWITCHING TIME TEST CIRCUIT



WAVEFORMS

